

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)			Docket Number: 3165.41USUI	Application Number: 10/723,382
			Applicant: MUNNS	
			Filing Date: 11/25/2003	Group Art Unit: 2815

O I P E S C I
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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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▼	6,489,628 B1	12/03/2002	Morizuka			

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<i>Mew</i>	6,583,454 B2	06/24/2003	Sheppard et al.			
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<i>Mew</i>		Khan, M. et al., "Properties and ion implantation of $Al_xGa_{1-x}N$ epitaxial single crystal films prepared by low pressure metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> , Vol. 43, No. 5, pp. 492-494 (September 1, 1983)
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<i>Munns</i>		Smorchkova, I. et al., "AlN/GaN and (Al,Ga)N/AlN/GaN two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy," <i>Journal of Applied Physics</i> , Vol. 90, No. 10, pp. 5196-5201 (November 15, 2001)
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